

PUMB9,125 Datasheet





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DiGi Electronics Part Number PUMB9,125-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PUMB9,125

Description TRANS PREBIAS 2PNP 50V 6TSSOP

Detailed Description Pre-Biased Bipolar Transistor (BJT) 2 PNP - Pre-Bias ed (Dual) 50V 100mA 180MHz 300mW Surface Mou

nt 6-TSSOP



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Manufacturer Product Number:	Manufacturer:
PUMB9,125	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
2 PNP - Pre-Biased (Dual)	100mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50V	10kOhms
Resistor - Emitter Base (R2):	DC Current Gain (hFE) (Min) @ Ic, Vce:
47kOhms	100 @ 5mA, 5V
Vce Saturation (Max) @ lb, lc:	Current - Collector Cutoff (Max):
100mV @ 250μA, 5mA	1μΑ
Frequency - Transition:	Power - Max:
180MHz	300mW
Grade:	Qualification:
Automotive	AEC-Q100
Mounting Type:	Package / Case:
Surface Mount	6-TSSOP, SC-88, SOT-363
Supplier Device Package:	Base Product Number:
6-TSSOP	PUMB9

Environmental & Export classification

8541.21.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



PUMB9

50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

4 January 2023

Product data sheet

1. General description

PNP/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PUMD9 NPN/NPN complement: PUMH9

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- Controlling IC inputs
- · Replaces general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Table II Quie	Table 1. Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V_{CEO}	collector-emitter voltage	open base		-	-	-50	V
Io	output current			-	-	-100	mA
R1	bias resistor 1 (input)			7	10	13	kΩ
R2/R1	bias resistor ratio			3.7	4.7	5.7	



50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	- □6 □5 □4	
3	O2	output (collector) TR2		R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		R2 R1
6	O1	output (collector) TR1	☐1 ☐2 ☐3 TSSOR((SOT363)	
			TSSOP6 (SOT363)	GND1 I1 O2
				006aaa212

6. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PUMB9		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>	

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMB9	B%9

[1] % = placeholder for manufacturing site code

50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

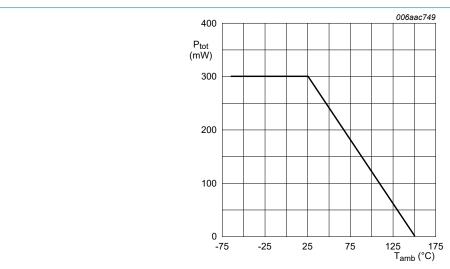
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or		•	'		
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V_{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
VI	input voltage	positive		-	6	V
		negative		-	-40	V
Io	output current			-	-100	mA
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	200	mW
Per device			•			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint

Fig. 1. Per device: Power derating curve

50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor		,				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device	'		,				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

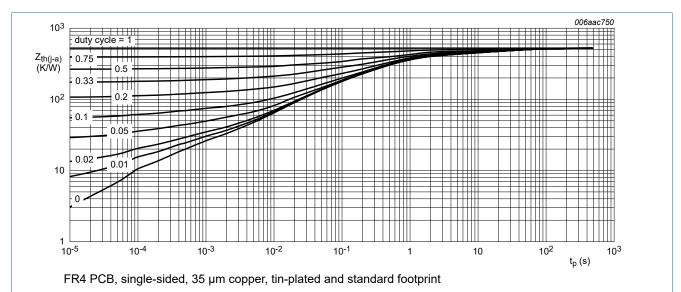


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

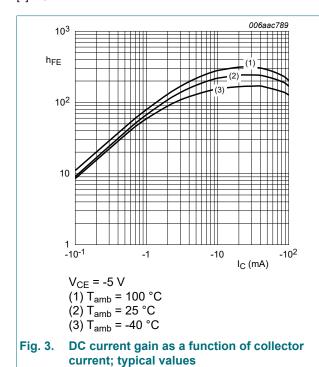
50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

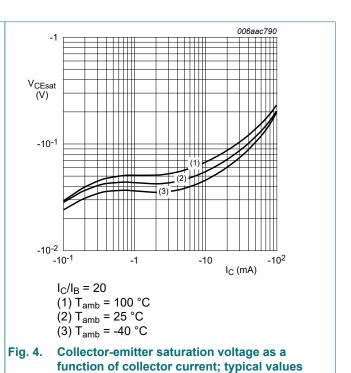
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or			I			
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = -100 \mu A; I_E = 0 A; T_{amb} = 25 °C$		-50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = -2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	-100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = -30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	-100	nA
	current	V _{CE} = -30 V; I _B = 0 A; T _j = 150 °C		-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	-150	μΑ
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -5 mA; T _{amb} = 25 °C		100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	-100	mV
V _{I(off)}	off-state input voltage	V_{CE} = -5 V; I_{C} = -100 μ A; T_{amb} = 25 °C		-	-0.7	-0.5	V
V _{I(on)}	on-state input voltage	V_{CE} = -0.3 V; I_{C} = -1 mA; T_{amb} = 25 °C		-1.4	-0.8	-	V
R1	bias resistor 1 (input)			7	10	13	kΩ
R2/R1	bias resistor ratio			3.7	4.7	5.7	
C _c	collector capacitance	/ _{CB} = -10 V; I _E = 0 A; i _e = 0 A; = 1 MHz; T _{amb} = 25 °C		-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; f = 100 \text{ MHz};$ [1 $I_{CE} = -5 \text{ C}$]		-	180	-	MHz

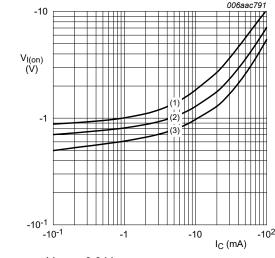
[1] Characteristics of built-in transistor



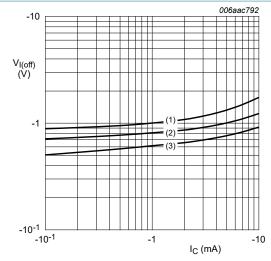


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50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω



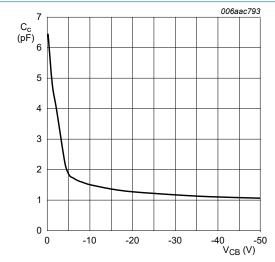
V_{CE} = -0.3 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C



V_{CE} = -5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 5. On-state input voltage as a function of collector | Fig. 6. current; typical values





 $f = 1 MHz; T_{amb} = 25 °C$

Fig. 7. Collector capacitance as a function of collectorbase voltage; typical values

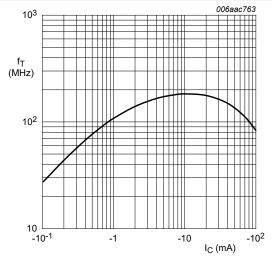


Fig. 8. Transition frequency as a function of collector current; typical values of built-in transistor

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50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Resistor calculation

Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

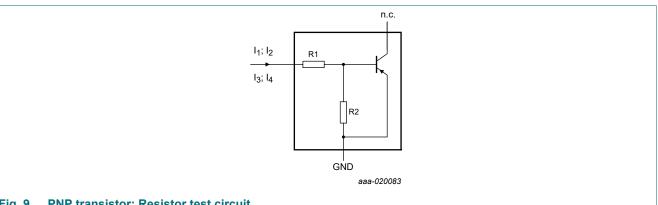


Fig. 9. **PNP transistor: Resistor test circuit**

Resistor test conditions

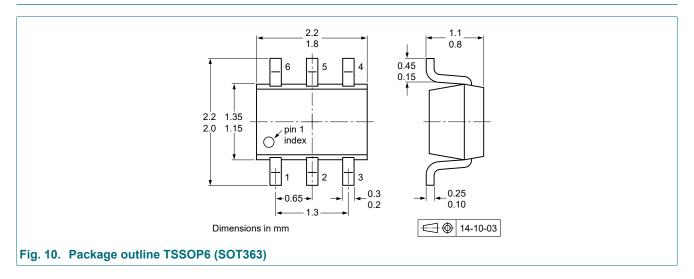
Table 8. Resistor test conditions

Type number	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I ₁	l ₂	l ₃	I ₄	
PUMB9	10	47	-140 μA	-90 μΑ	105 μΑ	55 µA	

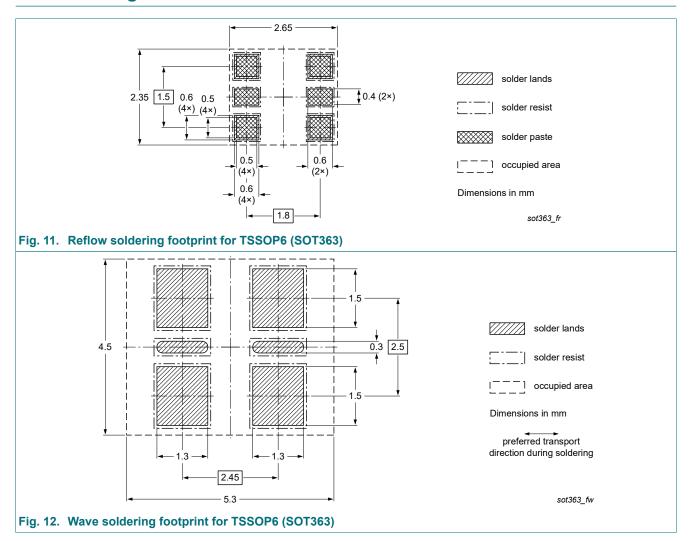
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50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

12. Package outline



13. Soldering



50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

14. Revision history

Table 9. Revision history

Table 5. Revision mistory					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PUMB9 v.4	20230104	Product data sheet	-	PEMB9_PUMB9 v.3	
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guideline Nexperia. Legal texts have been adapted to the new company name where appropriate. Family data sheet reduced to single type data sheet. Packing information is removed. 				
PEMB9_PUMB9 v.3	20111122	Product data sheet	-	PEMB9_PUMB9 v.2	
PEMB9_PUMB9 v.2	20031003	Product data sheet	-	PUMB9 v.1 PEMB9 v.1	
PUMB9 v.1	20030203	Objective specification	-	-	
PEMB9 v.1	20030107	Product specification	-	-	

50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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